National Semiconductor

February 1995

LM833 Dual Audio Operational Amplifier

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General Description

The LM833 is a dual general purpose operational amplifier designed with particular emphasis on performance in audio systems.

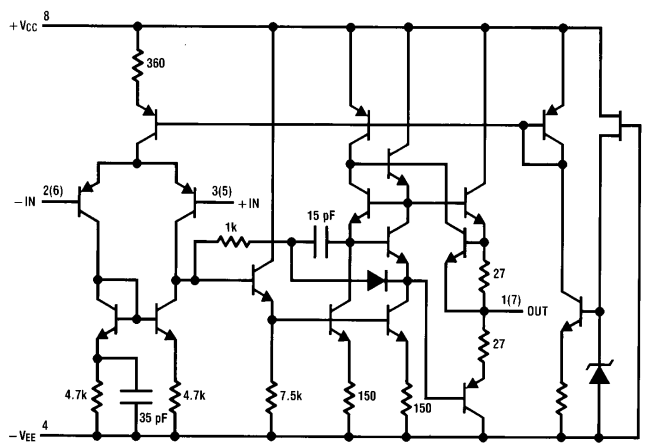
This dual amplifier IC utilizes new circuit and processing techniques to deliver low noise, high speed and wide bandwidth without increasing external components or decreasing stability. The LM833 is internally compensated for all closed loop gains and is therefore optimized for all preamp and high level stages in PCM and HiFi systems.

The LM833 is pin-for-pin compatible with industry standard dual operational amplifiers.

Features

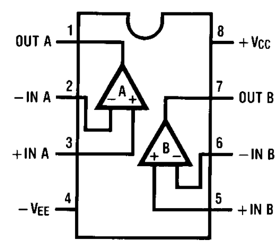
- Wide dynamic range — >140 dB
- Low input noise voltage — 4.5 nV/$\sqrt{Hz}$
- High slew rate — 7 V/μs (typ), 5 V/μs (min)
- High gain bandwidth product — 15 MHz (typ), 10 MHz (min)
- Wide power bandwidth — 120 kHz
- Low distortion — 0.002%
- Low offset voltage — 0.3 mV
- Large phase margin — 60°

Schematic Diagram (1/2 LM833)



TL/H/5218–1

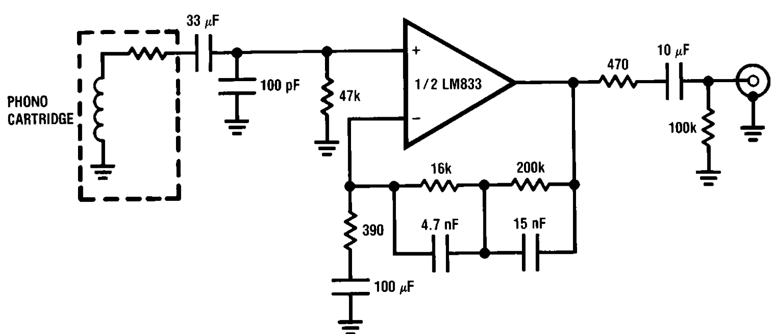
Connection Diagram



TL/H/5218–2

Order Number LM833M or LM833N
See NS Package Number
M08A or N08E

Typical Application RIAA Preamp



TL/H/5218–3

A_V = 35 dB	f = 1 kHz
E_n = 0.33 μV	A Weighted
S/N = 90 dB	A Weighted, V_{IN} = 10 mV @ f = 1 kHz

RRD-B30M75/Printed in U. S. A.

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage	$V_{CC}-V_{EE}$	36V
Differential Input Voltage (Note 1)	V_{ID}	±30V
Input Voltage Range (Note 1)	V_{IC}	±15V
Power Dissipation (Note 2)	P_D	500 mW
Operating Temperature Range	T_{OPR}	−40 ~ 85°C
Storage Temperature Range	T_{STG}	−60 ~ 150°C

Soldering Information
- Dual-In-Line Package
  - Soldering (10 seconds) 260°C
- Small Outline Package
  - Vapor Phase (60 seconds) 215°C
  - Infrared (15 seconds) 220°C

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

ESD tolerance (Note 3) 1600V

DC Electrical Characteristics (T_A = 25°C, V_S = ±15V)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OS}	Input Offset Voltage	R_S = 10Ω		0.3	5	mV
I_{OS}	Input Offset Current			10	200	nA
I_B	Input Bias Current			500	1000	nA
A_V	Voltage Gain	R_L = 2 kΩ, V_O = ±10V	90	110		dB
V_{OM}	Output Voltage Swing	R_L = 10 kΩ R_L = 2 kΩ	±12 ±10	±13.5 ±13.4		V V
V_{CM}	Input Common-Mode Range		±12	±14.0		V
CMRR	Common-Mode Rejection Ratio	V_{IN} = ±12V	80	100		dB
PSRR	Power Supply Rejection Ratio	V_S = 15~5V, −15~−5V	80	100		dB
I_Q	Supply Current	V_O = 0V, Both Amps		5	8	mA

AC Electrical Characteristics (T_A = 25°C, V_S = ±15V, R_L = 2 kΩ)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
SR	Slew Rate	R_L = 2 kΩ	5	7		V/μs
GBW	Gain Bandwidth Product	f = 100 kHz	10	15		MHz

Design Electrical Characteristics (T_A = 25°C, V_S = ±15V)

The following parameters are not tested or guaranteed.

Symbol	Parameter	Conditions	Typ	Units
$\Delta V_{OS}/\Delta T$	Average Temperature Coefficient of Input Offset Voltage		2	μV/°C
THD	Distortion	R_L = 2 kΩ, f = 20~20 kHz V_{OUT} = 3 Vrms, A_V = 1	0.002	%
e_n	Input Referred Noise Voltage	R_S = 100Ω, f = 1 kHz	4.5	$nV/\sqrt{Hz}$
i_n	Input Referred Noise Current	f = 1 kHz	0.7	$pA/\sqrt{Hz}$
PBW	Power Bandwidth	V_O = 27 V_{pp}, R_L = 2 kΩ, THD ≤ 1%	120	kHz
f_U	Unity Gain Frequency	Open Loop	9	MHz
ϕ_M	Phase Margin	Open Loop	60	deg
	Input Referred Cross Talk	f = 20~20 kHz	−120	dB

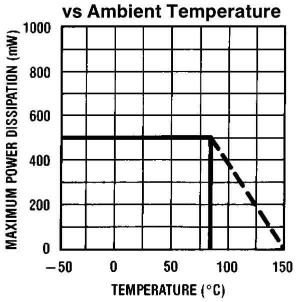
Note 1: If supply voltage is less than ±15V, it is equal to supply voltage.

Note 2: This is the permissible value at T_A ≤ 85°C.

Note 3: Human body model, 1.5 kΩ in series with 100 pF.

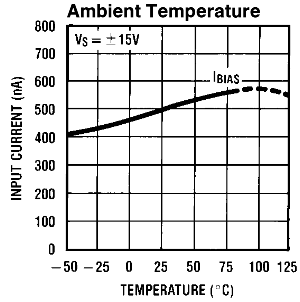
Typical Performance Characteristics

Maximum Power Dissipation vs Ambient Temperature



TL/H/5218–4

Input Bias Current vs Ambient Temperature



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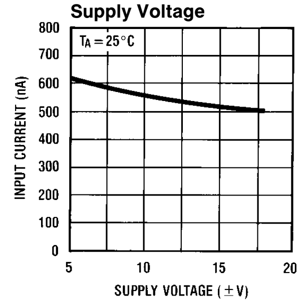
Input Bias Current vs Supply Voltage



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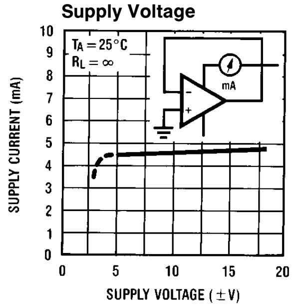
Supply Current vs Supply Voltage



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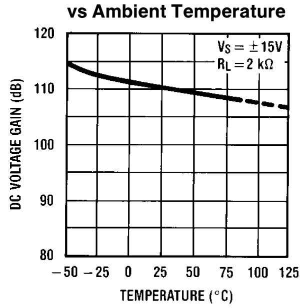
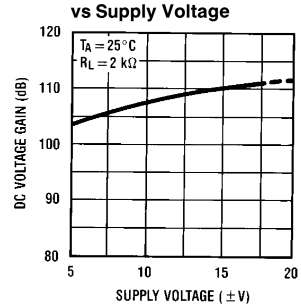
DC Voltage Gain vs Ambient Temperature



TL/H/5218–8

DC Voltage Gain vs Supply Voltage



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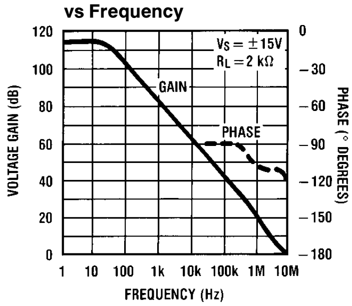
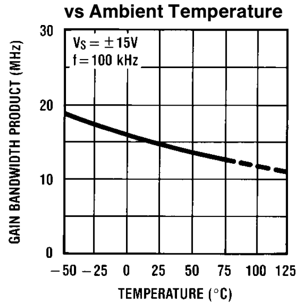
Voltage Gain & Phase vs Frequency



TL/H/5218–10

Gain Bandwidth Product vs Ambient Temperature



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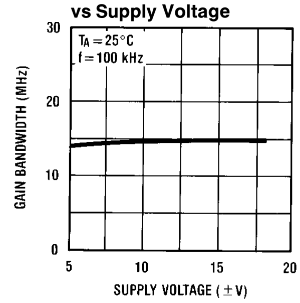
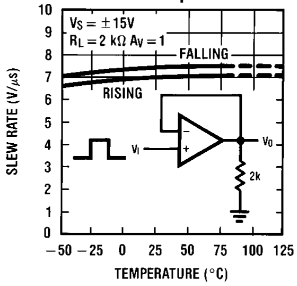
Gain Bandwidth vs Supply Voltage



TL/H/5218–12

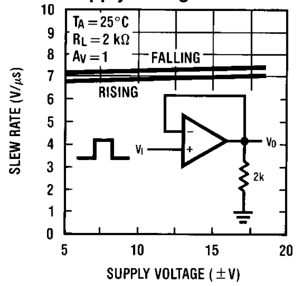
Typical Performance Characteristics (Continued)

Slew Rate vs Ambient Temperature



TL/H/5218–13

Slew Rate vs Supply Voltage



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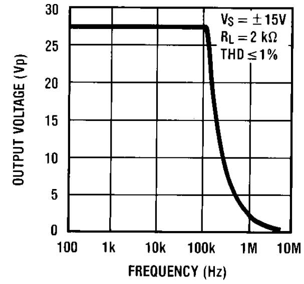
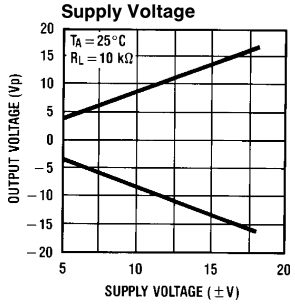
Power Bandwidth



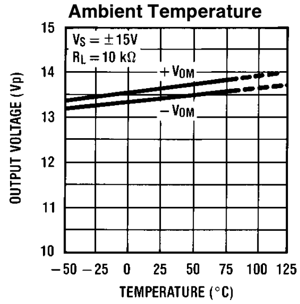
TL/H/5218–15

Maximum Output Voltage vs Supply Voltage



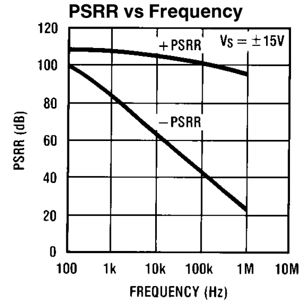
TL/H/5218–16

Maximum Output Voltage vs Ambient Temperature



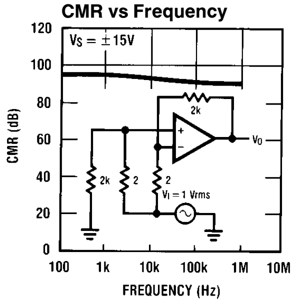
TL/H/5218–17

PSRR vs Frequency



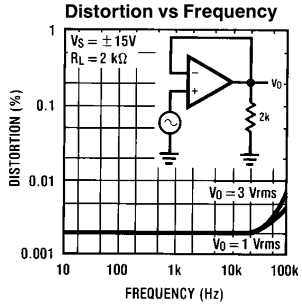
TL/H/5218–18

CMR vs Frequency



TL/H/5218–19

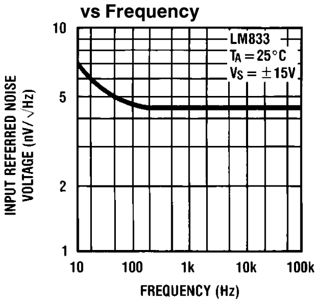
Distortion vs Frequency



TL/H/5218–20

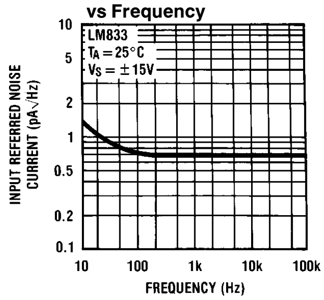
Typical Performance Characteristics (Continued)

Spot Noise Voltage vs Frequency



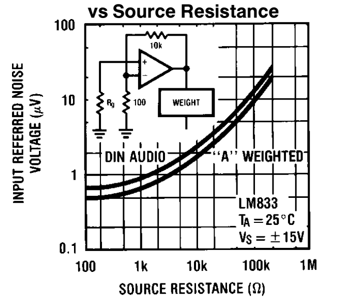
TL/H/5218–21

Spot Noise Current vs Frequency



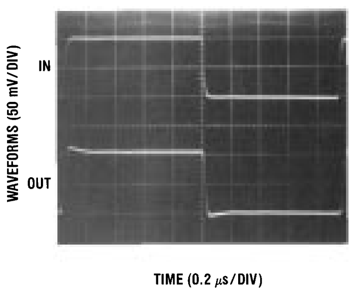
TL/H/5218–22

Input Referred Noise Voltage vs Source Resistance



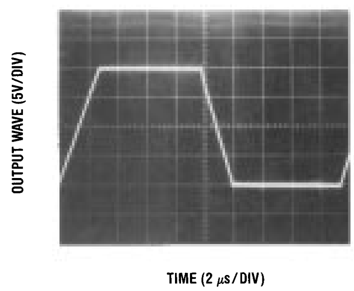
TL/H/5218–23

Noninverting Amp



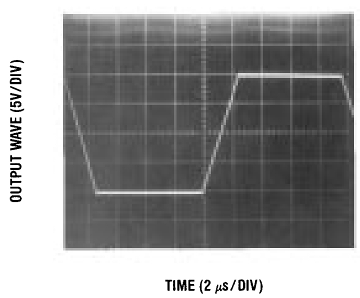
TL/H/5218–24

Noninverting Amp



TL/H/5218–25

Inverting Amp



TL/H/5218–26

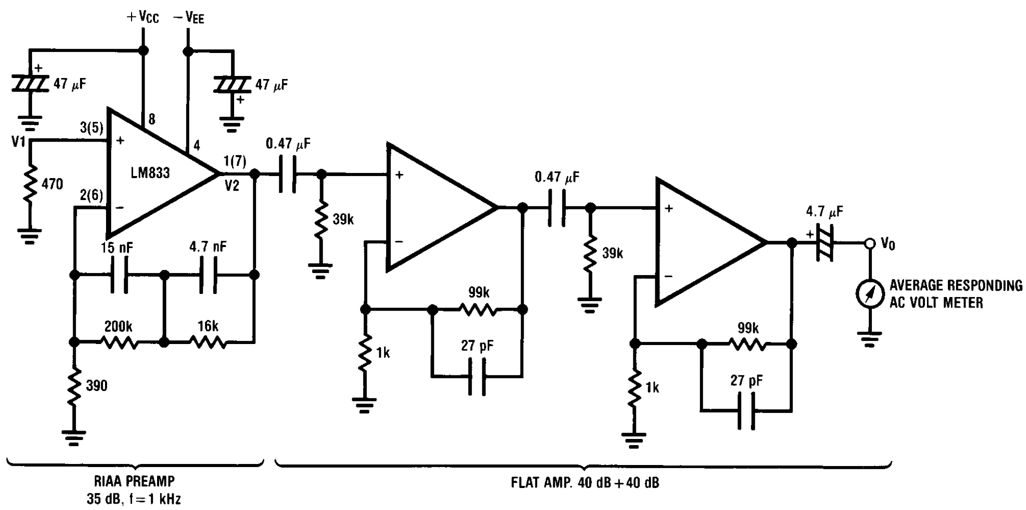
Application Hints

The LM833 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 50 pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

Capacitive loads greater than 50 pF must be isolated from the output. The most straightforward way to do this is to put a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

Noise Measurement Circuit

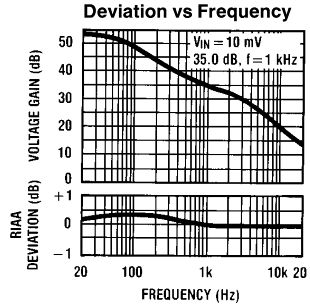
Complete shielding is required to prevent induced pick up from external sources. Always check with oscilloscope for power line noise.



TL/H/5218–27

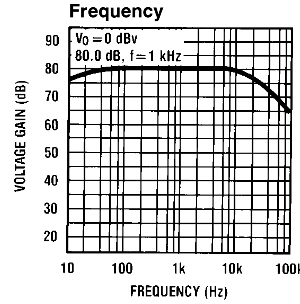
Total Gain: 115 dB @f = 1 kHz
Input Referred Noise Voltage: e_n = V0/560,000 (V)

RIAA Preamp Voltage Gain, RIAA Deviation vs Frequency



TL/H/5218–28

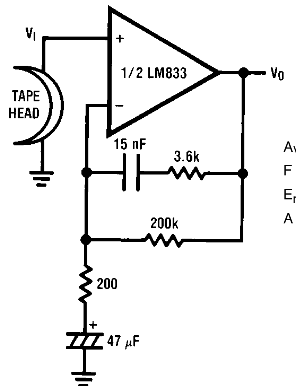
Flat Amp Voltage Gain vs Frequency



TL/H/5218–29

Typical Applications

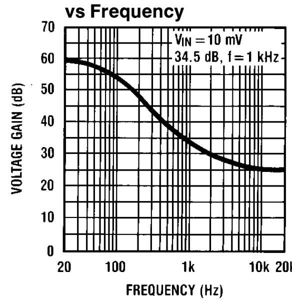
NAB Preamp



$A_V = 34.5$
F = 1 kHz
$E_n = 0.38\ \mu V$
A Weighted

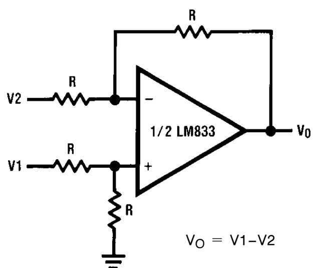
TL/H/5218–30

NAB Preamp Voltage Gain vs Frequency



TL/H/5218–31

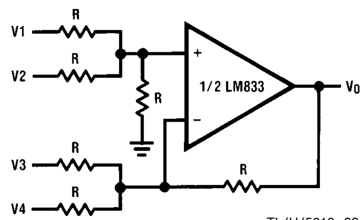
Balanced to Single Ended Converter



$V_O = V1 - V2$

TL/H/5218–32

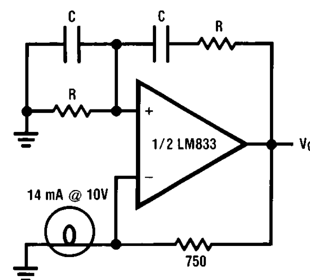
Adder/Subtracter



$V_O = V1 + V2 - V3 - V4$

TL/H/5218–33

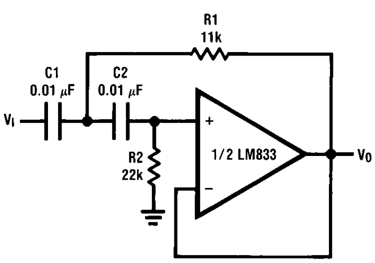
Sine Wave Oscillator



TL/H/5218–34

$$f_o = \frac{1}{2\pi RC}$$

Second Order High Pass Filter (Butterworth)



TL/H/5218–35

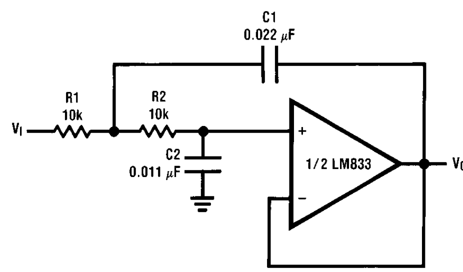
if C1 = C2 = C

$$R1 = \frac{\sqrt{2}}{2\omega_o C}$$

R2 = 2•R1

Illustration is f_0 = 1 kHz

Second Order Low Pass Filter (Butterworth)



TL/H/5218–36

if R1 = R2 = R

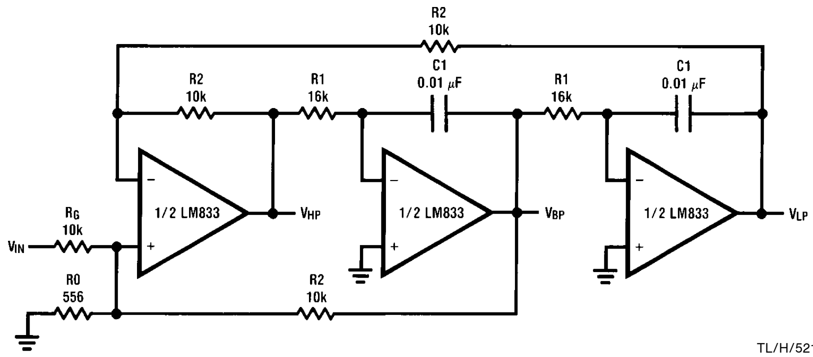
$$C1 = \frac{\sqrt{2}}{\omega_o R}$$

$$C2 = \frac{C1}{2}$$

Illustration is f_0 = 1 kHz

Typical Applications (Continued)

State Variable Filter

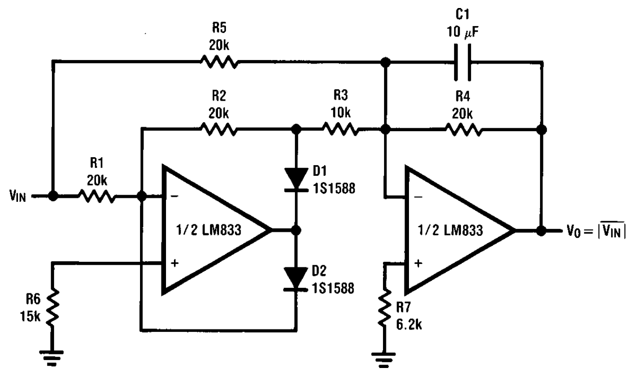


TL/H/5218–37

$f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$

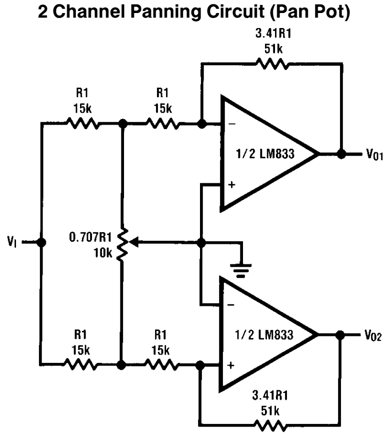
Illustration is $f_0 = 1$ kHz, $Q = 10$, $A_{BP} = 1$

AC/DC Converter



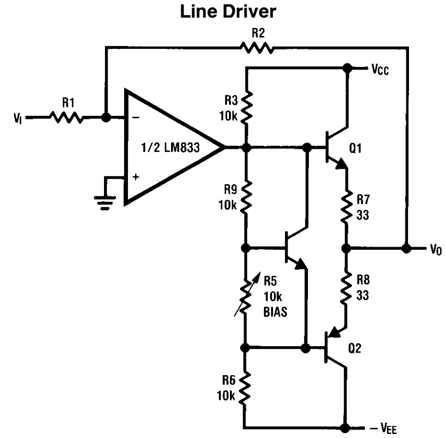
TL/H/5218–38

2 Channel Panning Circuit (Pan Pot)



TL/H/5218–39

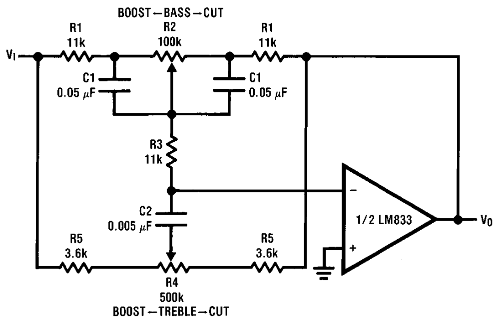
Line Driver



TL/H/5218–40

Typical Application (Continued)

Tone Control

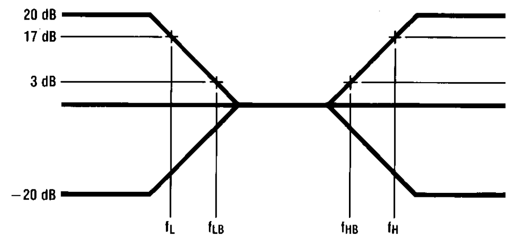


TL/H/5218–41

$$f_L = \frac{1}{2\pi R2C1},\ f_{LB} = \frac{1}{2\pi R1C1}$$

$$f_H = \frac{1}{2\pi R5C2},\ f_{HB} = \frac{1}{2\pi(R1 + R5 + 2R3)C2}$$

Illustration is:
f_L = 32 Hz, f_{LB} = 320 Hz
f_H = 11 kHz, f_{HB} = 1.1 kHz



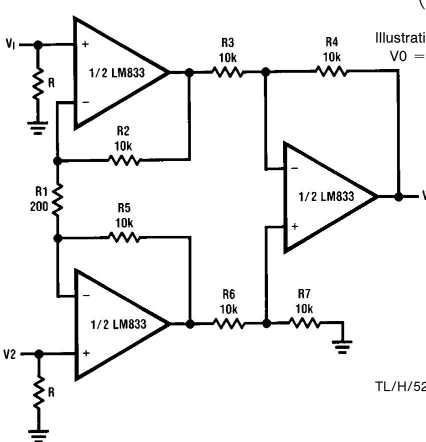
TL/H/5218–42

Balanced Input Mic Amp

If R2 = R5, R3 = R6, R4 = R7

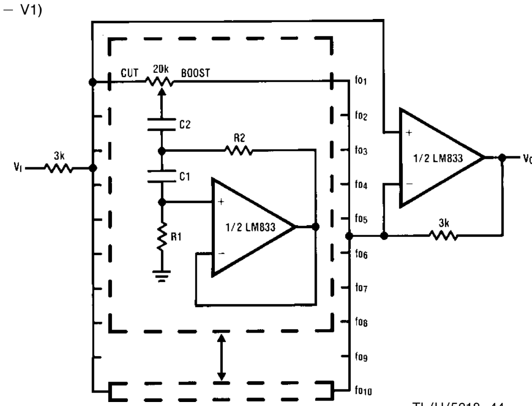
$$V0 = \left(1 + \frac{2R2}{R1}\right)\frac{R4}{R3}(V2 - V1)$$

Illustration is:
V0 = 101(V2 − V1)



TL/H/5218–43

10 Band Graphic Equalizer



TL/H/5218–44

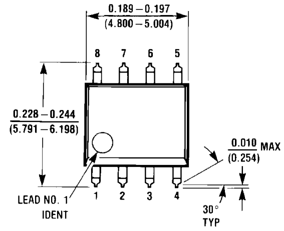
fo(Hz)	C_1	C_2	R_1	R_2
32	0.12μF	4.7μF	75kΩ	500Ω
64	0.056μF	3.3μF	68kΩ	510Ω
125	0.033μF	1.5μF	62kΩ	510Ω
250	0.015μF	0.82μF	68kΩ	470Ω
500	8200pF	0.39μF	62kΩ	470Ω
1k	3900pF	0.22μF	68kΩ	470Ω
2k	2000pF	0.1μF	68kΩ	470Ω
4k	1100pF	0.056μF	62kΩ	470Ω
8k	510pF	0.022μF	68kΩ	510Ω
16k	330pF	0.012μF	51kΩ	510Ω

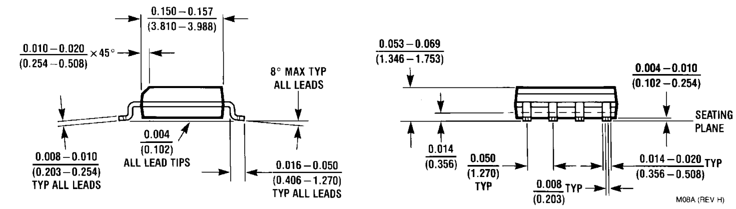
At volume of change = ±12 dB
Q = 1.7

Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2–61

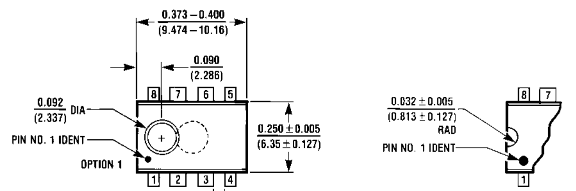
Physical Dimensions inches (millimeters)

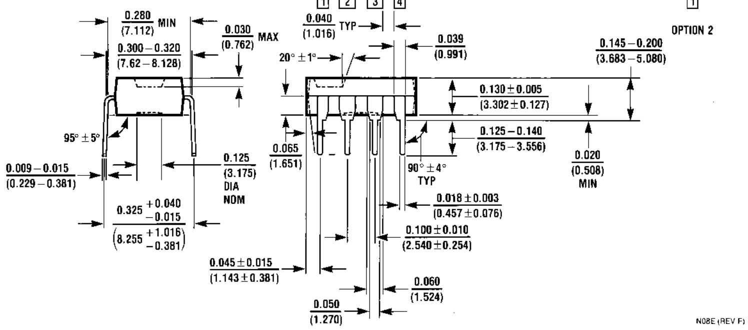
Small Outline Package (M)
Order Number LM833M
NS Package Number M08A





Molded Dual-In-Line Package (N)
Order Number LM833N
NS Package Number N08E





LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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